3.3 V / 5.0 V Ultra-Low Skew 1:4 Clock Fanout Buffer

Description

The NB3N551 is a low skew 1-to 4 clock fanout buffer, designed for clock distribution in mind. The NB3N551 specifically guarantees low output-to-output skew. Optimal design, layout and processing minimize skew within a device and from device to device.

The output enable (OE) pin three-states the outputs when low.

Features

- Input/Output Clock Frequency up to 180 MHz
- Low Skew Outputs (50 ps typical)
- RMS Phase Jitter (12 kHz 20 MHz): 43 fs (Typical)
- Output goes to Three-State Mode via OE
- Operating Range: $V_{DD} = 3.0 \text{ V}$ to 5.5 V
- Ideal for Networking Clocks
- Packaged in 8-pin SOIC
- Industrial Temperature Range
- These are Pb-Free Devices

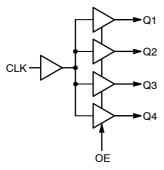


Figure 1. Block Diagram



ON Semiconductor®

http://onsemi.com



CASE 751



MARKING

3N551 = Specific Device Code A = Assembly Location

L = Wafer Lot Y = Year W = Work Week ■ = Pb-Free Package



DFN8 MN SUFFIX CASE 506AA



6K = Specific Device Code

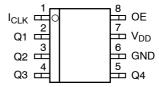
M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping [†]
NB3N551DG	SOIC-8 (Pb-Free)	98 Units/Rail
NB3N551DR2G	SOIC-8 (Pb-Free)	2500/Tape & Reel
NB3N551MNR4G	DFN-8 (Pb-Free)	1000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 1. OE, OUTPUT ENABLE FUNCTION

OE	Function
0	Disable
1	Enable

Table 2. PIN DESCRIPTION

Pin#	Name	Туре	Description
1	I _{CLK}	(LV)CMOS/(LV)TTL Input	Clock Input. Internal pull—up resistor.
2	Q1	(LV)CMOS/(LV)TTL Output	Clock Output 1
3	Q2	(LV)CMOS/(LV)TTL Output	Clock Output 2
4	Q3	(LV)CMOS/(LV)TTL Output	Clock Output 3
5	Q4	(LV)CMOS/(LV)TTL Output	Clock Output 4
6	GND	Power	Negative supply voltage; Connect to ground, 0 V
7	V_{DD}	Power	Positive supply voltage (3.0 V to 5.5 V)
8	OE	(LV)CMOS/(LV)TTL Input	Output Enable for the clock outputs. Outputs are enabled when HIGH or when left open; OE pin has internal pull-up resistor. Three-states outputs when LOW.
-	EP	Thermal Exposed Pad	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Units
V_{DD}	Positive Power Supply	GND = 0 V	-	7.0	V
V _I /V _O	Input/Output Voltage	t ≤ 1.5 ns	-	GND-1.5 \leq V _I /V _O \leq V _{DD} +1.5	V
T _A	Operating Temperature Range, Industrial	-	-	≥ -40 to ≤ +85	°C
T _{stg}	Storage Temperature Range	-	-	−65 to +150	°C
θЈА	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8	190 130	°C/W °C/W
θЈС	Thermal Resistance (Junction-to-Case)	(Note 1)	SOIC-8	41 to 44	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN8	35 to 40	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

Table 4. ATTRIBUTES

Charac	Value			
ESD Protection	Human Body Model Machine Model	> 4 kV > 200 V		
Moisture Sensitivity, Indefinite T	Level 1			
Flammability Rating	UL-94 code V-0 @ 0.125 in			
Transistor Count	531 Devices			
Meets or Exceeds JEDEC Standard EIA/JESD78 IC Latchup Test				

^{2.} For additional Moisture Sensitivity information, refer to Application Note AND8003/D.

Table 5. DC CHARACTERISTICS (V_{DD} = 3.0 V to 3.6 V, GND = 0 V, T_A = -40° C to $+85^{\circ}$ C) (Note 3)

Symbol	Characteristic	Min	Тур	Max	Unit
I _{DD}	Power Supply Current @ 135 MHz, No Load, V _{DD} = 3.3 V	-	20	40	mA
V _{OH}	Output HIGH Voltage – I _{OH} = –25 mA, V _{DD} = 3.3 V	2.4	-	-	٧
V _{OL}	Output LOW Voltage – I _{OL} = 25 mA	-	-	0.4	V
V _{OH}	Output HIGH Voltage – I _{OH} = –12 mA (CMOS level)	V _{DD} - 0.4	-	-	V
V _{IH} , I _{CLK}	Input HIGH Voltage, I _{CLK}	(V _{DD} /2)+0.7	-	3.8	V
V _{IL,} I _{CLK}	Input LOW Voltage, I _{CLK}	-	-	(V _{DD} /2)-0.7	٧
V _{IH,} OE	Input HIGH Voltage, OE	2.0	-	VDD	V
V _{IL,} OE	Input LOW Voltage, OE	0	-	0.8	V
ZO	Nominal Output Impedance	_	20	-	Ω
RPU	Input Pull-up Resistor, OE	_	220	-	kΩ
CIN	Input Capacitance, OE	_	5.0	-	pF
IOS	Short Circuit Current	_	± 50	-	mA

DC CHARACTERISTICS (V_{DD} = 4.5 V to 5.5 V, GND = 0 V, T_A = -40°C to +85°C) (Note 3)

Symbol	Characteristic	Min	Тур	Max	Unit
I _{DD}	Power Supply Current @ 135 MHz, No Load, V _{DD} = 5.0 V	-	50	95	mA
V _{OH}	Output HIGH Voltage – I _{OH} = –35 mA	2.4	-	-	V
V _{OL}	Output LOW Voltage – I _{OL} = 35 mA	=	-	0.4	V
V _{OH}	Output HIGH Voltage – I _{OH} = –12 mA (CMOS level)	V _{DD} - 0.4	-	-	V
V _{IH} , I _{CLK}	Input HIGH Voltage, I _{CLK}	(V _{DD} /2) + 1	-	5.5	V
V _{IL,} I _{CLK}	Input LOW Voltage, I _{CLK}	-	-	(V _{DD} /2) – 1	V
V _{IH,} OE	Input HIGH Voltage, OE	2.0	-	V_{DD}	V
V _{IL,} OE	Input LOW Voltage, OE	0	-	0.8	V
ZO	Nominal Output Impedance	-	20	-	Ω
RPU	Input Pull-up Resistor, OE	=	220	-	kΩ
CIN	Input Capacitance, OE	-	5.0	-	pF
IOS	Short Circuit Current	=	±80	-	mA

Table 6. AC CHARACTERISTICS ($V_{DD} = 3.0 \text{ V to } 5.5 \text{ V}$, GND = 0 V, $T_A = -40 ^{\circ}\text{C}$ to $+85 ^{\circ}\text{C}$) (Note 3)

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
f _{in}	Input Frequency		-	-	180	MHz
t _{jitter} (φ)	RMS Phase Jitter (Integrated 12 kHz – 20 MHz) (See Figures 2 and 3)	f _{carrier} = 25 MHz f _{carrier} = 50 MHz	-	43 16	- -	fs
t _{jitter (pd)}	Period Jitter (RMS, 1σ)		-	2.0	-	ps
t _r /t _f	Output rise and fall times; 0.8 V to 2.0 V		-	0.5	1.0	ns
t _{pd}	Propagation Delay, CLK to Qn, 0 – 180 MHz, (Note 4)		1.5	3.0	6.0	ns
t _{skew}	Output-to-Output Skew; (Note 5)		_	50	160	ps

Outputs loaded with external R_L = 33-Ω series resistor and C_L = 15 pF to GND for proper operation. Duty cycle out = duty in. A 0.01 μF decoupling capacitor should be connected between V_{DD} and GND. A 33 Ω series terminating resistor may be used on each clock output if the trace is longer than 1 inch.
 Measured with rail-to-rail input clock.
 Measured on rising edges at V_{DD} ÷ 2.

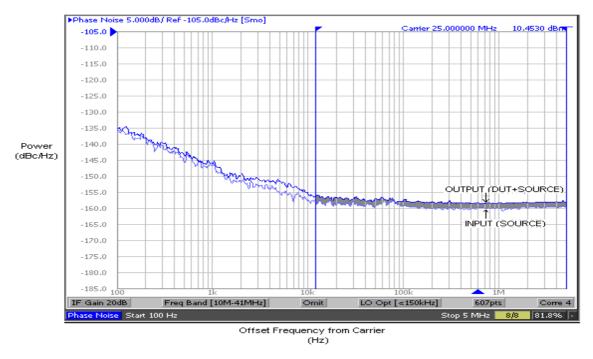


Figure 2. Phase Noise Plot at 25 MHz at an Operating Voltage of 3.3 V, Room Temperature

The above plot captured using Agilent E5052A shows Additive Phase Noise of the NB3N551 device measured with an input source generated by Agilent E8663B. The RMS phase jitter contributed by the device (integrated between 12 kHz to 20 MHz; as shown in the shaded region of the plot) is 43 fs (RMS Jitter of the input source is 203.31 fs and Output (DUT+Source) is 247.06 fs).

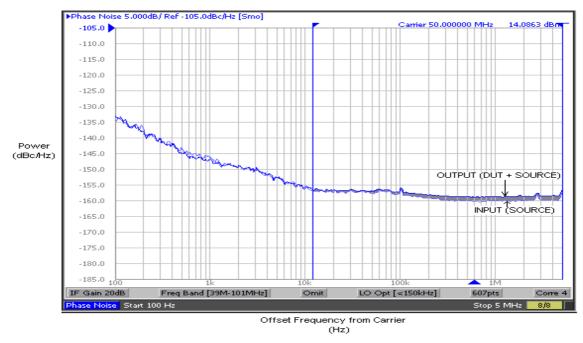
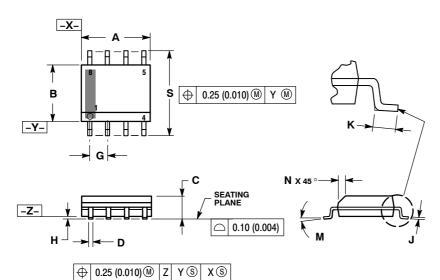


Figure 3. Phase Noise Plot at 50 MHz at an Operating Voltage of 5 V, Room Temperature

The above plot captured using Agilent E5052A shows Additive Phase Noise of the NB3N551 device measured with an input source generated by Agilent E8663B. The RMS phase jitter contributed by the device (integrated between 12 kHz to 20 MHz; as shown in the shaded region of the plot) is 16 fs (RMS Jitter of the input source is 104.08 fs and Output (DUT + Source) is 119.77 fs).

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 **ISSUE AJ**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

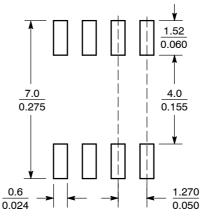
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
 PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 6. 751–01 THRU 751–06 ARE OBSOLETE. NEW
 STANDARD IS 751–07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	BSC	0.05	0 BSC
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

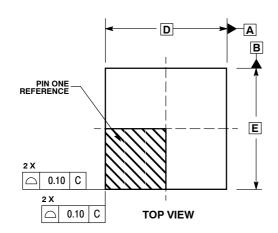


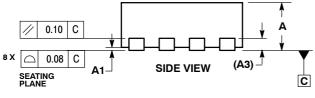
 $\left(\frac{\text{mm}}{\text{inches}}\right)$ SCALE 6:1

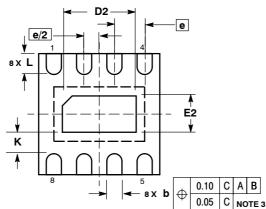
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

DFN8 CASE 506AA-01 ISSUE D







BOTTOM VIEW

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
 COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
А3	0.20	REF		
b	0.20	0.30		
D	2.00	BSC		
D2	1.10	1.30		
E	2.00	BSC		
E2	0.70	0.90		
е	0.50 BSC			
K	0.20			
L	0.25	0.35		

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and war engineer trademarks of semiconductor components industries, Ite (SciLLC) solitate services are injective to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative